Docket No. 53074-025

## **Declaration For Patent Application**

## **English Language Declaration**

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled

BUFFER LAYER AND GROWTH METHOD FOR SUBSEQUENT EPITAXIAL GROWTH OF III-V NITRIDE SEMICONDUCTORS

the specification of which

	neck one)			
×	is attached hereto.			
	was filed on	as Unite	d States Application No.	or PCT International
ele kak	Application Number			
Ŋ	and was amended on _			
H.J		(if	applicable)	
I h	ereby state that I have re luding the claims, as ame	eviewed and understand the ended by any amendment re	contents of the above in eferred to above.	dentified specification,
kno	cknowledge the duty to common to me to be materication 1.56.	disclose to the United States al to patentability as define	s Patent and Trademarked in Title 37, Code of	Office all information Federal Regulations,
Se any list inv	ction 365(b) of any forei y PCT International applic ed below and have also i	rity benefits under Title 35 gn application(s) for patent cation which designated at ledentified below, by checking International application ha	or inventor's certificate east one country other tl g the box, any foreign ap	or Section 365(a) of nan the United States, oplication for patent or
Pri	or Foreign Application(s)			Priority Not Claimed
(Nu	ımber)	(Country)	(Day/Month/Year Filed)	
(Nu	ımber)	(Country)	(Day/Month/Year Filed)	
(Nu	ımber)	(Country)	(Day/Month/Year Filed)	

I hereby claim the benefit under application(s) listed below:	35 U.S.C. Section 119(	e) of any United States provisional
(Application Serial No.)	(Filing Date)	-
(Application Serial No.)	(Filing Date)	-
(Application Serial No.)	(Filing Date)	-
insofar as the subject matter of each United States or PCT International a	ch of the claims of this apapplication in the manner the duty to disclose to the to be material to patent between the filing date or	g the United States, listed below and, oplication is not disclosed in the prior provided by the first paragraph of 35 United States Patent and Trademark tability as defined in Title 37, CFR f the prior application and the national
(Application Serial No.)	(Filing Date)	(Status) (patented, pending, abandoned)
(Application Serial No.)	(Filing Date)	(Status) (patented, pending, abandoned)
(Application Serial No.)	(Filing Date)	(Status) (patented, pending, abandoned)

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

Sole or first inventor's signature	Date
Tizo Veden	July 11, 20
Residence 600 Sharon Park Drive, #A201, Menlo Park, CA 94025	
Citizenship	
Japan	
Post Office Address	
600 Sharon Park Drive, #A201, Menlo Park, CA 94025	
Full name of second inventor, if any	
Second inventor's signature	Date
Decidence	
Residence	
Citizenship	
Post Office Address	
Sol Office Address	
Full name of third inventor, if any	
Third inventor's signature	Date
Residence	
244	
Citizenship	
Post Office Address	
Full name of fourth inventor, if any	
Fourth inventor's signature	Date
Residence	
Citizenship	
Post Office Address	
OST OTHER VIOLESS	
	The state of the s